

CUSTOMER	NO. SST 6427
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	DATE

 SUBJECT TRANSISTOR, NPN ,SILICON
 ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unless Otherwise Specified)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV _{CBO}	I _C = 100 uA	40			V
BV _{CEO}	I _C = 10 mA	40			V
BV _{EBO}	I _E = 10 uA	12			V
I _{CBO}	V _{CB} = 30 V			50	nA
I _{CEO}	V _{CE} = 25 V			1.0	uA
I _{EBO}	V _{BE} = 10 V			50	nA
H _{FE}	I _C = 10 mA, V _{CE} = 5.0 V	10,000		100,000	
H _{FE}	I _C = 100 mA, V _{CE} = 5.0 V	20,000		200,000	
H _{FE}	I _C = 500 mA, V _{CE} = 5.0 V	14,000		140,000	
V _{CE(SAT)}	I _C = 50 mA, I _B = 0.5 mA		0.71	1.2	V
V _{CE(SAT)}	I _C = 500 mA, I _B = 0.5 mA		0.9	1.5	V
V _{BE(SAT)}	I _C = 500 mA, I _B = 0.5 mA		1.52	2.0	V
V _{BE(ON)}	I _C = 50 mA, V _{CE} = 5.0 V		1.24	1.75	V
C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1.0 MHz		5.4	7.0	pF
C _{ib}	V _{BE} = 1.0 V, I _C = 0, f = 1.0 MHz		10	15	pF
h _{ie}	I _C = 10 mA, V _{CE} = 5 V, f = 1.0KHz	50		1000	KΩ
h _{fe}	I _C = 10 mA, V _{CE} = 5 V, f = 1.0KHz	10,000			
h _{oe}	I _C = 10 mA, V _{CE} = 5 V, f = 1.0KHz			1000	umhos
NF	I _C = 1.0 mA, V _{CE} = 5 V, R _S = 100KΩ f = 10 KHz to 15.7 KHz		3.0	10	dB

ROHM ELECTRONICS
 3034 Owen Drive, Antioch, TN 37013
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APPROVAL

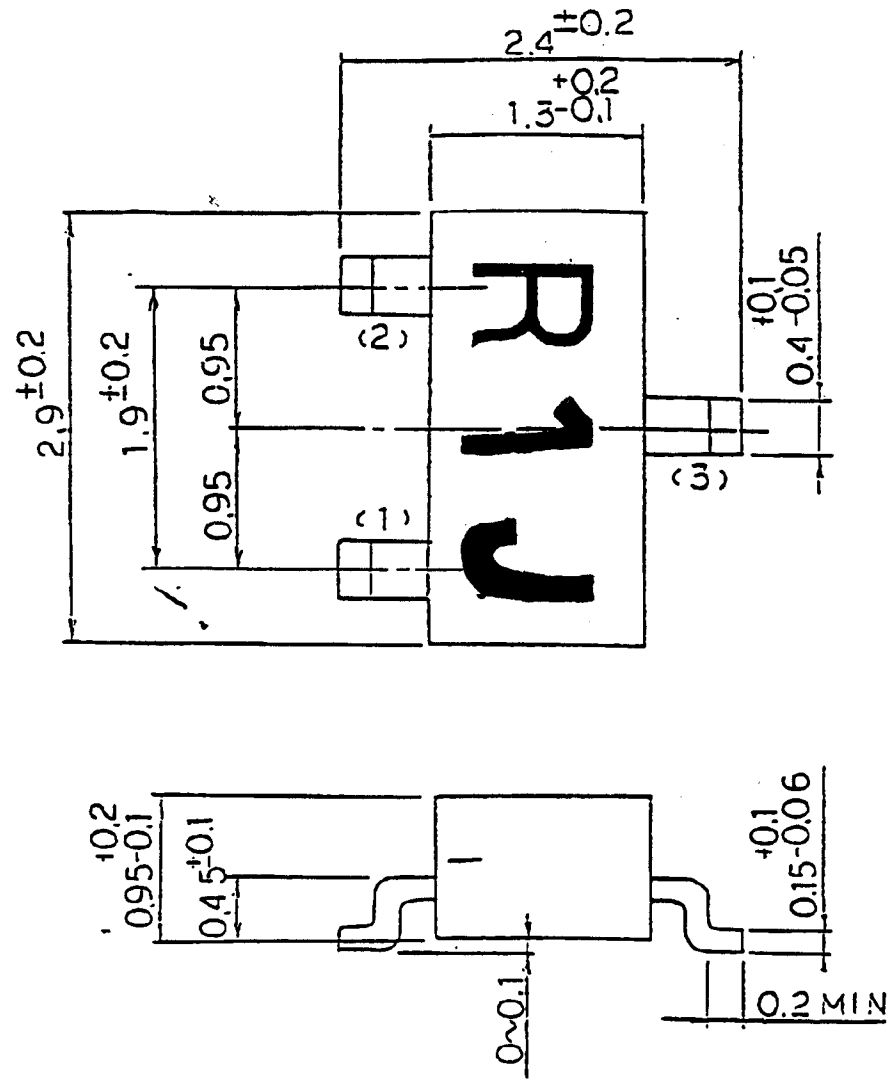
T. Smith
 80-18-99

CHECK

EDW
 5/24/99

DESIGN

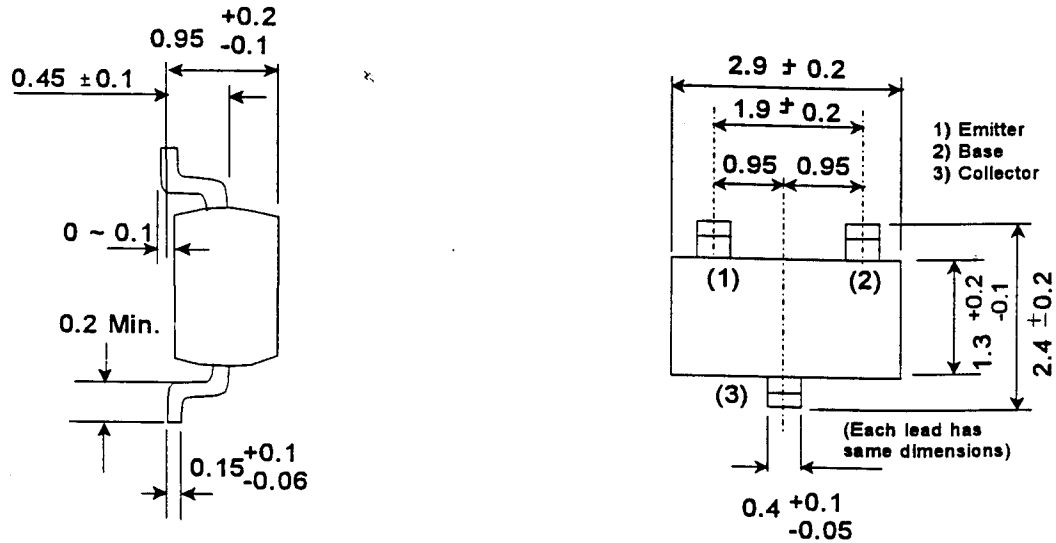
MASTER



UNIT : mm

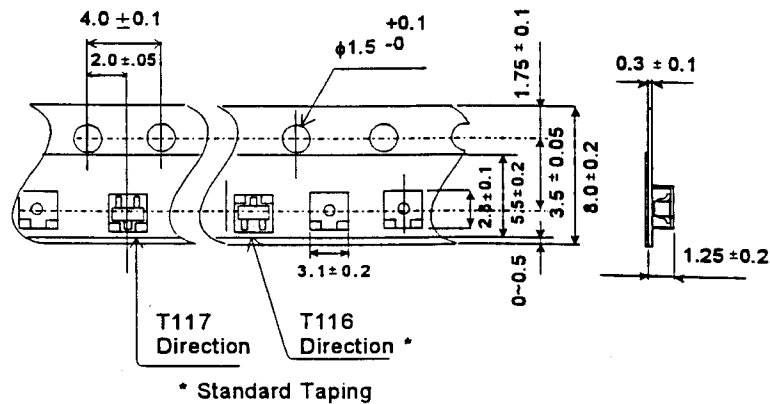
- (1) Emitter
- (2) Base
- (3) Collector

SST (EUROPEAN SOT23) PACKAGE



Unit: mm

- 1) Emitter
- 2) Base
- 3) Collector



MASTER